ABSTRACT

ELECTRONIC DEVICE AND METHOD OF MANUFACTURING THE SAME

A semiconductor memory may include: variable resistance layers and insulating layers alternately stacked; conductive pillars passing through the variable resistance layers and the insulating layers; a slit insulating layer passing through the insulating layers and extending in a first direction; and conductive layers interposed between the slit insulating layer and the variable resistance layers. The variable resistance layers may remain in an amorphous state during a program operation.

FIG. 2A